

**BCW61B**

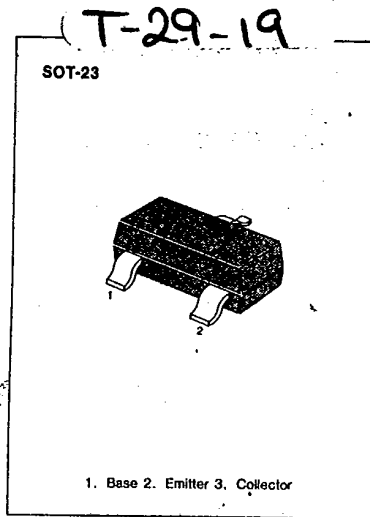
**PNP EPITAXIAL SILICON TRANSISTOR**

**GENERAL PURPOSE TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	32	V
Collector-Emitter Voltage	V <sub>CEO</sub>	32	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	100	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C

• Refer to MMBT5086 for graphs



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**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 2mA, I <sub>B</sub> = 0	32		V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 1μA, I <sub>C</sub> = 0	5		V
Collector Cutoff Current	I <sub>CES</sub>	V <sub>CE</sub> = 32V, V <sub>BE</sub> = 0		20	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10μA	20		
		V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA	140	310	
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 50mA	80		
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.25mA		0.25	V
Base-Emitter Saturation Voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 50mA, I <sub>B</sub> = 1.25mA		0.55	V
		I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.25mA	0.6	0.85	V
Base-Emitter On Voltage	V <sub>BE (on)</sub>	I <sub>C</sub> = 50mA, I <sub>B</sub> = 1.25mA	0.68	1.05	V
		I <sub>C</sub> = 2mA, V <sub>CE</sub> = 5V	0.6	0.75	V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0 f = 1MHz		6	pF
Noise Figure	NF	I <sub>C</sub> = 0.2mA, V <sub>CE</sub> = 5V R <sub>S</sub> = 2KΩ, f = 1KHz		6	dB
Turn On Time	t <sub>on</sub>	I <sub>C</sub> = 10mA, I <sub>B1</sub> = 1mA		150	ns
Turn Off Time	t <sub>off</sub>	I <sub>B2</sub> = 1mA, V <sub>BB</sub> = 3.6V R <sub>L</sub> = 990Ω		800	ns

Marking

